

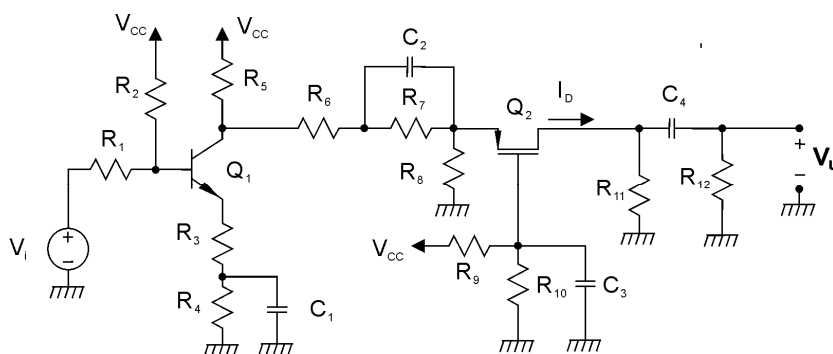
ELETTRONICA DIGITALE

Corso di Laurea in Ingegneria Informatica

Prova scritta del 16 aprile 2015

Esercizio A

| | |
|-----------------------------|-------------------------------|
| $R_2 = 176 \text{ k}\Omega$ | $R_{10} = 10 \text{ k}\Omega$ |
| $R_3 = 250 \text{ }\Omega$ | $R_{11} = 4 \text{ k}\Omega$ |
| $R_4 = 4 \text{ k}\Omega$ | $R_{12} = 30 \text{ k}\Omega$ |
| $R_5 = 1 \text{ k}\Omega$ | $C_1 = 15 \text{ nF}$ |
| $R_6 = 50 \text{ }\Omega$ | $C_2 = 220 \text{ nF}$ |
| $R_7 = 550 \text{ }\Omega$ | $C_3 = 1 \text{ }\mu\text{F}$ |
| $R_8 = 24 \text{ k}\Omega$ | $C_4 = 680 \text{ pF}$ |
| $R_9 = 10 \text{ k}\Omega$ | $V_{CC} = 18 \text{ V}$ |



Q_1 è un transistor BJT BC109B resistivo con $h_{re} = h_{oe} = 0$; Q_2 è un transistor MOS a canale p resistivo, con la corrente di drain in saturazione data da $I_D = k(V_{GS} - V_T)^2$ con $k = 0.5 \text{ mA/V}^2$ e $V_T = -1 \text{ V}$.

Con riferimento al circuito in figura:

- 1) Calcolare il valore della resistenza R_1 in modo che, in condizioni di riposo, la tensione sul drain di Q_2 sia 8 V. Determinare, inoltre, il punto di riposo dei due transistori e verificare la saturazione di Q_2 . (R: $R_1 = 213440 \text{ }\Omega$)
- 2) Determinare V_U/V_i alle frequenze per le quali C_1, C_2, C_3, C_4 possono essere considerati dei corto circuiti. (R: $V_U/V_i = -1.73$)
- 3) (**Solo per 12 CFU**) Determinare la funzione di trasferimento V_U/V_i e tracciarne il diagramma di Bode quotato asintotico del modulo. (R: $f_{z1} = 2652.58 \text{ Hz}$; $f_{p1} = 20746.39 \text{ Hz}$; $f_{z2} = 1315.33 \text{ Hz}$; $f_{p2} = 1785.15 \text{ Hz}$; $f_{z4} = 0 \text{ Hz}$; $f_{p4} = 6883.86 \text{ Hz}$)

Esercizio B

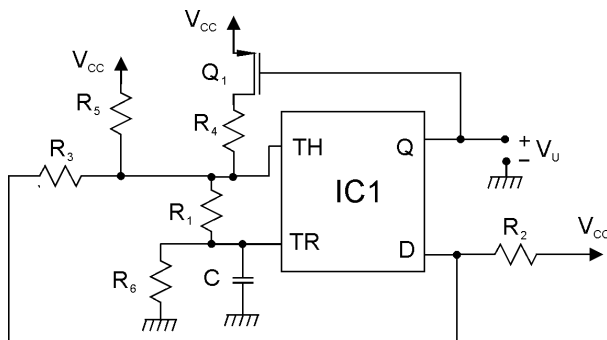
Progettare una porta logica in tecnologia CMOS, utilizzando la tecnica della pull-up network e della pull-down network, che implementi la funzione logica:

$$Y = (\overline{A+C})(\overline{B}D + \overline{D}E) + \overline{C}(\overline{B} + A\overline{D}E) + A\overline{E}$$

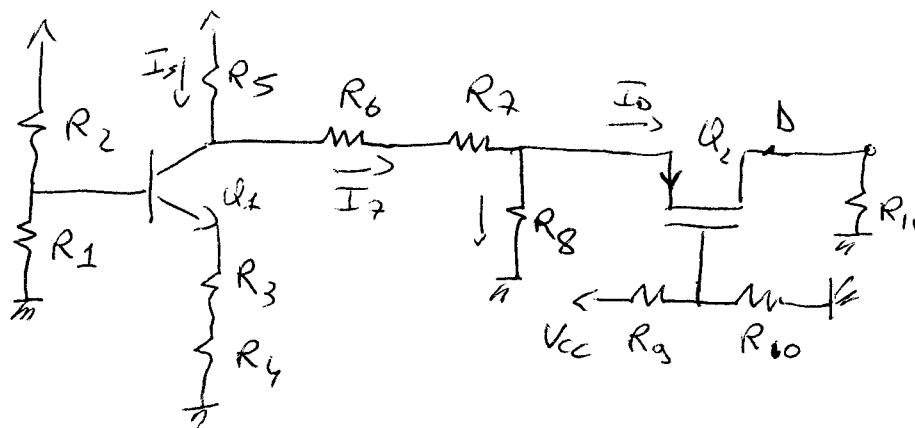
Determinare il numero dei transistori necessari e disegnarne lo schema completo. Dimensionare inoltre il rapporto (W/L) di tutti i transistori, assumendo, per l'inverter di base, W/L pari a 2 per il MOS a canale n e pari a 5 per quello a canale p. Si specifichino i dettagli della procedura di dimensionamento dei transistori.

Esercizio C

| | |
|----------------------------|---------------------------|
| $R_1 = 400 \text{ }\Omega$ | $R_5 = 2 \text{ k}\Omega$ |
| $R_2 = 1 \text{ k}\Omega$ | $R_6 = 5 \text{ k}\Omega$ |
| $R_3 = 1 \text{ k}\Omega$ | $C = 100 \text{ nF}$ |
| $R_4 = 30 \text{ k}\Omega$ | $V_{CC} = 6 \text{ V}$ |



Il circuito IC_1 è un NE555 alimentato a $V_{CC} = 6 \text{ V}$, Q_1 ha una $R_{on} = 0$ e $V_T = -1 \text{ V}$. Determinare la frequenza del segnale di uscita del multivibratore in figura. (R: $f = 4751.87 \text{ Hz}$)



$$1) V_D = 8V$$

$$I_D = \frac{V_D}{R_{11}} = \frac{8}{4 \times 10^3} = 2 \text{ mA}$$

$$I_D = K(V_{GS} - V_T)^2 \Rightarrow (V_{GS} - V_T) = -\sqrt{\frac{I_D}{K}} = -2V$$

$$\Rightarrow V_{GS} = -2 + V_T = -3V$$

$$V_G = V_{CC} \frac{R_{10}}{R_{10} + R_9} = 9V$$

$$\Rightarrow V_S = V_G - V_{GS} = 9 + 3 = 12V$$

$$V_{DS} = V_D - V_S = 8 - 12 = -4V < V_{GS} - V_T = -2V \Rightarrow \text{SAT. OK}$$

$$I_8 = \frac{V_S}{R_8} = \frac{12}{24 \times 10^3} = 0.5 \text{ mA}$$

$$I_7 = I_8 + I_D = 2.5 \text{ mA}$$

$$V_C = I_7(R_6 + R_7) + V_S = 13.5V$$

$$I_5 = \frac{V_{CC} - V_C}{R_5} = 4.5 \text{ mA}$$

$$I_C = I_5 - I_7 = 2 \text{ mA}$$

$$\text{hp: } I_B \ll I_E \Rightarrow I_E \approx I_C$$

$$V_E = I_C(R_3 + R_4) = 8.5V$$

$$V_{CE} = V_C - V_E = 13.5 - 8.5 = 5V$$

$$I_B = \frac{I_C}{h_{FE}} = 6.836 \times 10^{-6} \text{ A}$$

$$Q_2: \begin{cases} V_{DS} = -4V \\ V_{GS} = -3V \\ I_D = 2 \text{ mA} \\ g_m = 2K|V_{GS} - V_T| = 2 \times 10^{-3} \frac{A}{V} \end{cases}$$

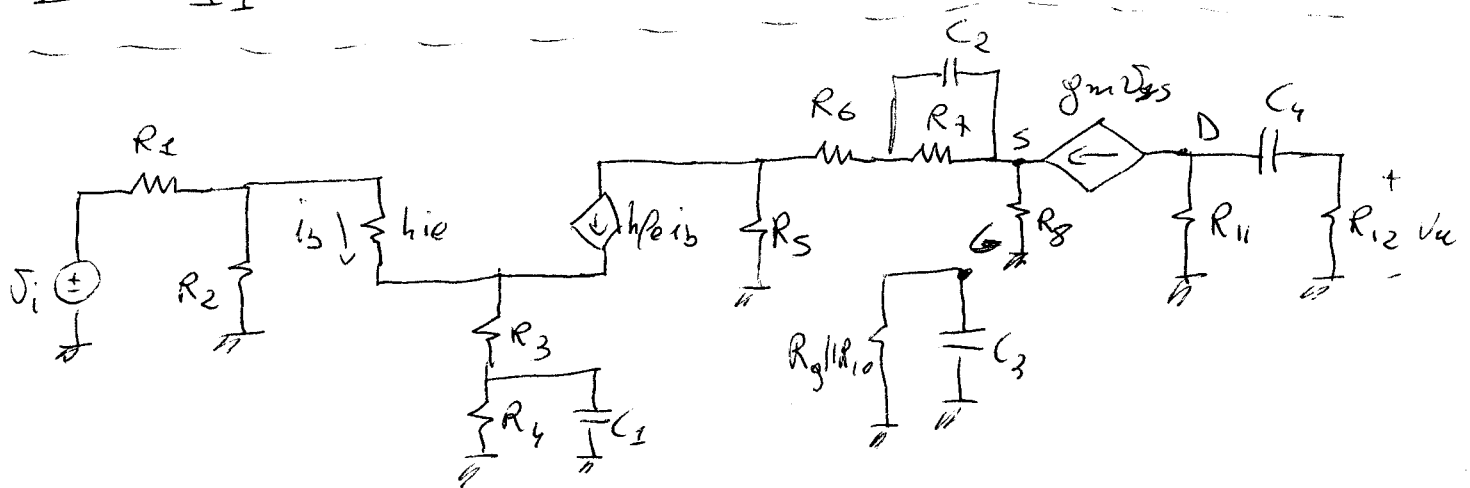
$$Q_1: \begin{cases} V_{CE} = 5V \\ I_C = 2 \text{ mA} \\ I_B = 6.836 \mu A \\ h_{FE} = 290 \\ h_{pe} = 300 \\ h_{ie} = 4800 \Omega \end{cases}$$

$$V_E + V_F = 9.2V$$

$$I_2 = \frac{V_{CC} - V_B}{R_2} = 50 \mu A$$

$$I_1 = I_2 - I_B = 43.3 \mu A$$

$$R_1 = \frac{V_B}{I_1} = \underline{\underline{213440 \Omega}}$$



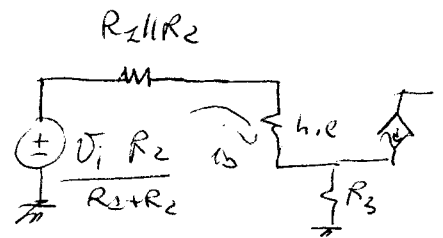
A_{CB}

$$V_u = (R_{11} \parallel R_{12})(-g_m V_{gs})$$

$$V_g = \phi$$

$$V_d = (-h_{fe} i_b) \frac{R_5}{R_5 + R_6 + R_8 \parallel \frac{1}{g_m}} \left(R_8 \parallel \frac{1}{g_m} \right)$$

$$i_b = V_i \frac{R_2}{R_1 + R_2} \frac{1}{R_1 \parallel R_2 + h_{ie} + R_3(h_{fe} + 1)}$$



$$A_{CB} = +g_m (R_{11} \parallel R_{12}) (-h_{fe}) \frac{R_5}{R_5 + R_6 + R_8 \parallel \frac{1}{g_m}} \frac{R_8 \parallel \frac{1}{g_m}}{R_1 + R_2} \frac{1}{R_1 \parallel R_2 + h_{ie} + R_3(h_{fe} + 1)}$$

2117.647
 318.0345
 0.4519
 5.665×10^{-6}

$$= -1.7247 \quad (|A_{CB}|_{dB} = 4.73 \text{ dB})$$

CONDENSATORE $C_1 = 15 \text{ nF}$

$$f_{z1} = \frac{1}{2\pi C_1 R_4} = \underline{2652.58 \text{ Hz}}$$

$$f_{p1} = \frac{1}{2\pi C_1 R_{V1}} = \underline{20746.33 \text{ Hz}}$$

$$R_{V1} = R_4 \parallel \left[R_3 + \frac{h_{ie} + R_1 \parallel R_2}{h_{\beta e} + 1} \right] = 511.43 \Omega$$

CONDENSATORE $C_2 = 220 \text{ nF}$

$$f_{z2} = \frac{1}{2\pi C_2 R_2} = \underline{1315.33 \text{ Hz}}$$

$$f_{p2} = \frac{1}{2\pi C_2 R_{V2}} = \underline{1785.15 \text{ Hz}}$$

$$R_{V2} = R_7 \parallel \left[R_6 + R_5 + R_8 \parallel \frac{1}{g_m} \right] = 405.25 \Omega$$

CONDENSATORE C_3

$$f_{z3} = f_{p3}$$

CONDENSATORE $C_4 = 680 \text{ pF}$

$$f_{z4} = \phi$$

$$f_{p4} = \frac{1}{2\pi C_4 R_{V4}} = 6883.86 \text{ Hz}$$

$$R_{V4} = R_{11} + R_{12} = 39 \text{ k}\Omega$$

④

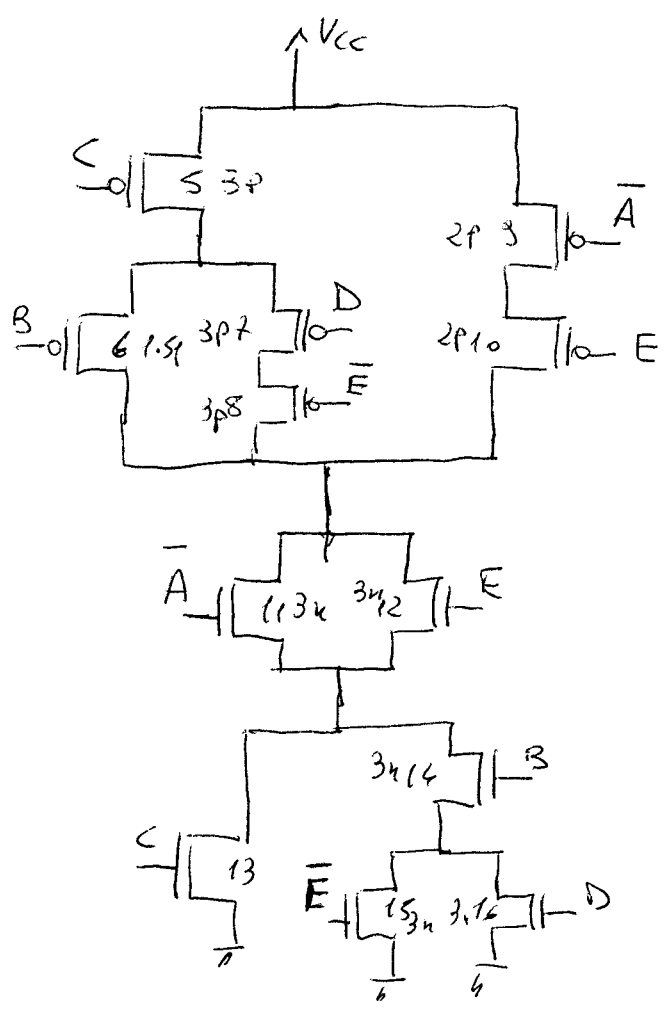
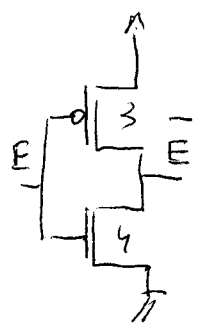
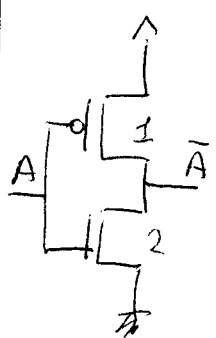
$$= (\overline{A+C})(\overline{B}D + \overline{D}E) + \overline{C}(\overline{B} + A\overline{D}E) + A\overline{E} =$$

$$= \overline{A}\overline{C}(\overline{B}D + \overline{D}E) + \overline{C}\overline{B} + A\overline{C}\overline{D}E + A\overline{E} =$$

$$= \underbrace{\overline{A}\overline{B}\overline{C}D}_x + \underbrace{\overline{A}\overline{C}\overline{D}E}_0 + \underbrace{\overline{C}\overline{B}}_x + \underbrace{A\overline{C}\overline{D}E}_0 + A\overline{E} =$$

$$= \overline{B}\overline{C} + \overline{C}\overline{D}E + A\overline{E} =$$

$$= \overline{C}(\overline{B} + \overline{D}E) + A\overline{E} \Rightarrow 16 \text{ MOSFET}$$



$Q_1, Q_3 : p$

$Q_2, Q_4 : n$

$Q_5, Q_7, Q_8 : 3p$

$Q_6 : 1.5p$

$Q_9, Q_{10} : 2p$

$Q_{11}, Q_{14}, Q_{16} : 3n$

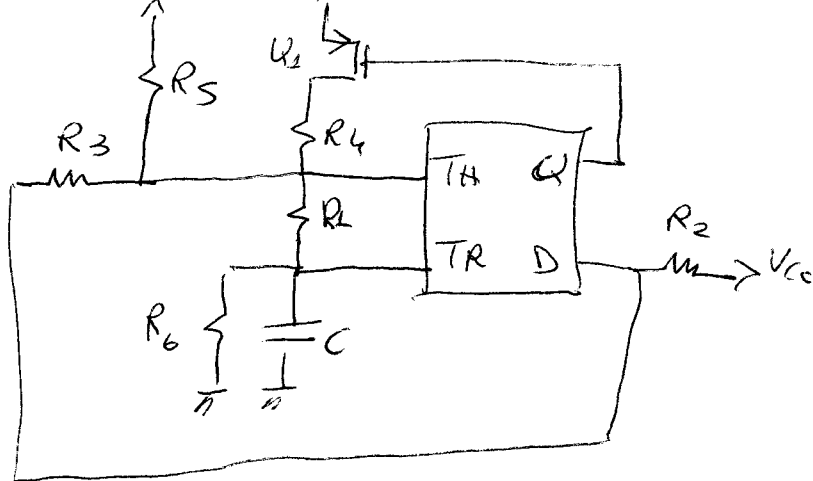
$Q_{11}, Q_{14}, Q_{15} : 3n$

$Q_{12}, Q_{14}, Q_{16} : \Rightarrow Q_{12} : 3n$

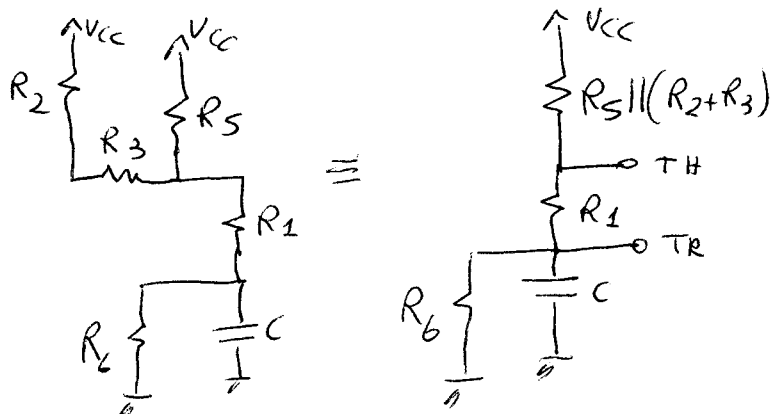
$Q_{11}, Q_{13} \Rightarrow Q_{13} = 1.5n$

$$\frac{1}{x} + \frac{1}{3n} = \frac{1}{n}$$

$$\frac{1}{x} = \frac{2}{3n} \Rightarrow x = \frac{3}{2}n = 1.5n$$



$U_1 = 1 \quad D = HI \quad V_{G1} = V_{CC} \quad V_{S1} = V_{CC} \Rightarrow V_{GS} = 0 > V_T \Rightarrow Q_1 \text{ OFF}$



$$V_i = \frac{1}{3} V_{CC} = \underline{2V}$$

$$V_f = V_{CC} \frac{R_6}{R_6 + R_1 + R_5 \parallel (R_2 + R_3)}$$

$$\underline{V_f = 4.6875}$$

$$V_{TH} = \frac{2}{3} V_{CC} = 4V$$

$$I_1 = \frac{V_{CC} - V_{TH}}{R_5 \parallel (R_2 + R_3)} = \frac{2}{1000} = 2 \text{ mA}$$

$$\underline{V_{con}} = V_{TH} - R_1 I_1 = \underline{3.2V}$$

$$V_i < V_{con} < V_f$$

$$2V > 3.2V > 4.6875V$$

$$R_{vc} = R_6 \parallel [R_1 + R_5 \parallel (R_2 + R_3)] = 1093.75 \Omega$$

OK

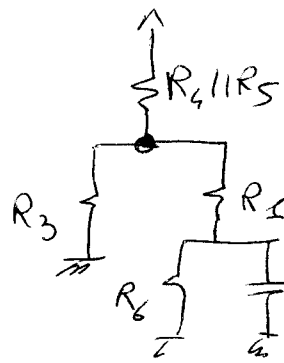
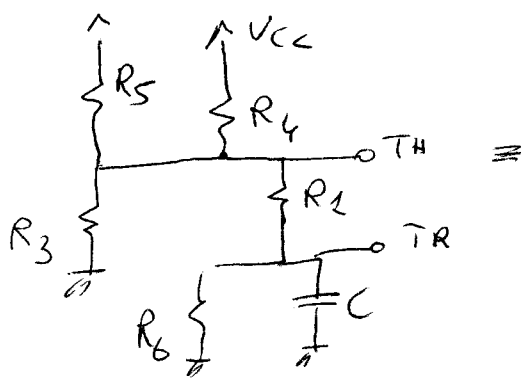
$$\tau_1 = C_1 R_{vc} = 109.375 \mu s$$

$$T_1 = \tau_1 \ln \left[\frac{V_i - V_f}{V_{con} - V_f} \right] = 64.697 \mu s$$

$$D=0 \quad V_G = 0V \\ V_S = V_{CC} = 6V$$

$$V_{GS} = -V_{CC} < V_T \Rightarrow W_L \text{ ON}$$

(6)



$$V_i = \underline{\underline{3.2V}} \\ V_{con} = \underline{\underline{2V}}$$

$$V_f = V_{CC} \frac{R_3 \parallel (R_1 + R_6)}{(R_4 \parallel R_5) + [R_3 \parallel (R_1 + R_6)]} \frac{R_6}{R_1 + R_6} = 1.724V$$

$$V_i > V_{con} > V_f \quad [3.2V > 2V > 1.724V \text{ OK}]$$

$$R_{vc2} = R_6 \parallel [R_1 + R_4 \parallel R_5 \parallel R_3] = 869.25 \Omega$$

$$\tau_2 = C R_{vc2} = 86.92 \mu s$$

$$T_2 = \tau_2 \ln \left(\frac{V_i - V_f}{V_{con} - V_f} \right) = 145.74 \mu s$$

$$T = T_1 + T_2 = 210.443 \mu s$$

$$f = \frac{1}{T} = 4751.865 \text{ Hz}$$